

Vortex in Coulomb blockaded granule: parity effect suppression and electron pumping

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*To the memory of
Nikolai Kopnin*

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Institute for physics of microstructures



Russian academy of sciences

Collaboration with N.B. Kopnin

By the time when we met with N. B. Kopnin for the first time in Dec 2012 we had been coauthors for 3 years and have 2 common papers.

Then I had a great opportunity to work with him personally for a half of a year being his PostDoc. It was a great collaboration. The ideas discussed at that time actuate till now.

The main idea of this talk came up after the discussions with N.B. Kopnin.



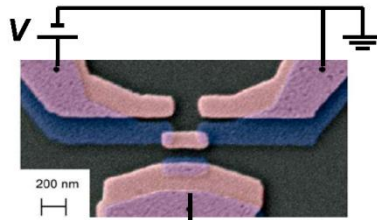
Outline:

- **Electron pumping in SET:**
Main ideas, ingredients, and results
- **Parity effect and its suppression by vortex penetration.**
- **New principle of electron pumping in SET**
Parity effect tuning
- **Possible realization**
Time-varying magnetic field
- **Summary**

Outline:

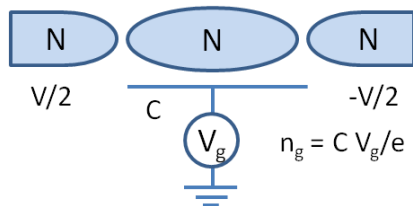
- **Electron pumping in SET:**
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Single electron transistor (SET)

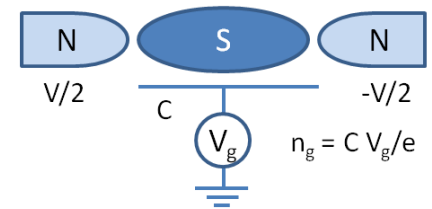
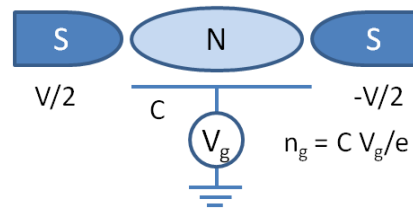


J.P. Pekola et al Nat. Phys. (2008)

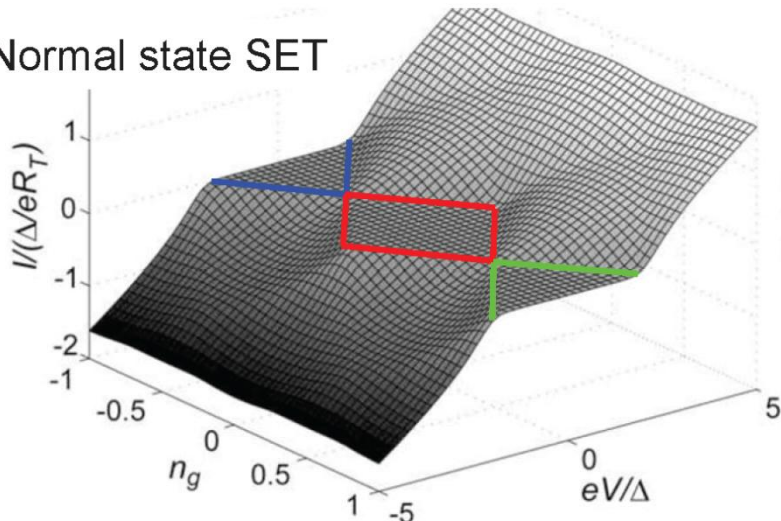
Normal state SET



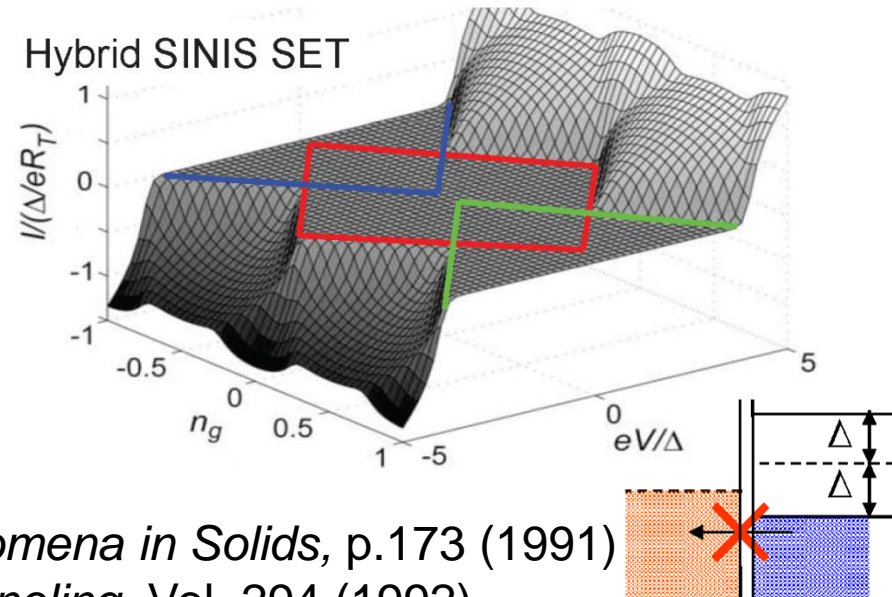
Hybrid SINIS or NISIN SET



Normal state SET



Hybrid SINIS SET

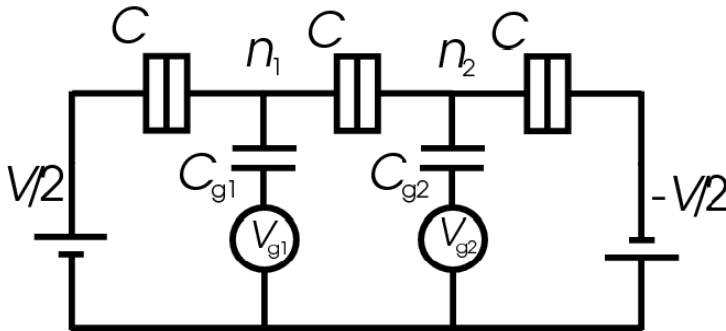


Averin, Likharev *Mesoscopic Phenomena in Solids*, p.173 (1991)

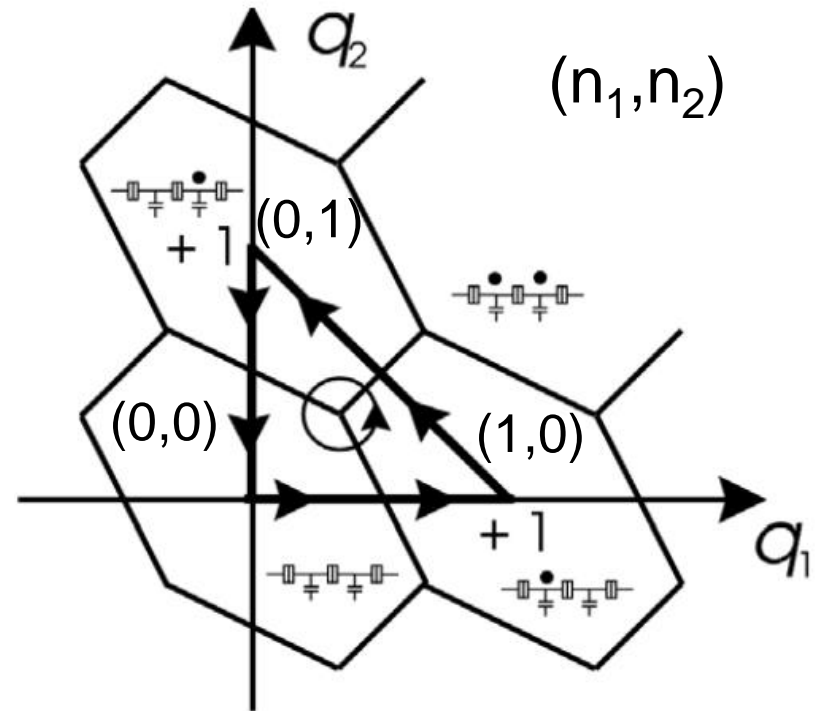
Averin, Nazarov *Single Charge Tunneling*, Vol. 294 (1992)

Single electron transistors as a turnstile

Cyclic operation (frequency f) of gates, $q_i = C_{gi} V_{gi}/e$, transports charge through the system



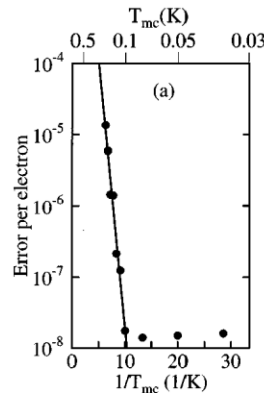
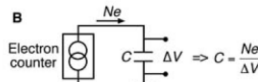
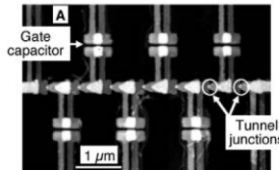
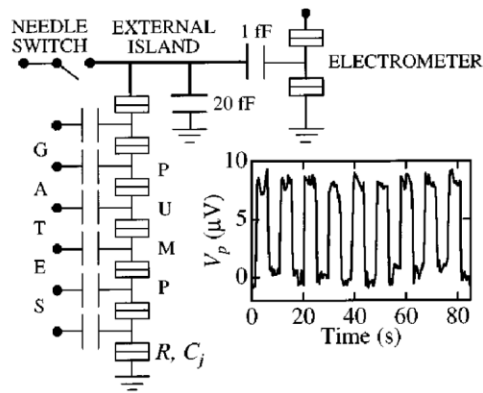
$$I = ef$$



H. Pothier et al., EPL 17, 249 (1992)

Single electron sources

Towards frequency-to-current conversion



Semiconductor devices, travelling wave or quantum dots:

Shilton et al. 1996

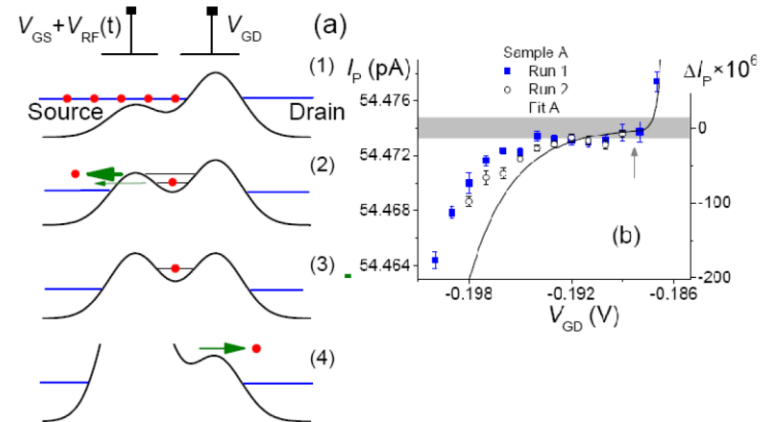
Fujiwara et al. 2004

Blumenthal et al. 2007

Fève et al., 2007

Kaestner et al. 2007

Giblin et al., 2010



Normal single-electron pump: $I = ef$

Geerligs et al. 1990, Pothier et al. 1992,

Keller et al. 1996, Lotkhov et al. 2000

High accuracy but still slow: $I \ll 10$ pA

Fully superconducting devices:

Several versions

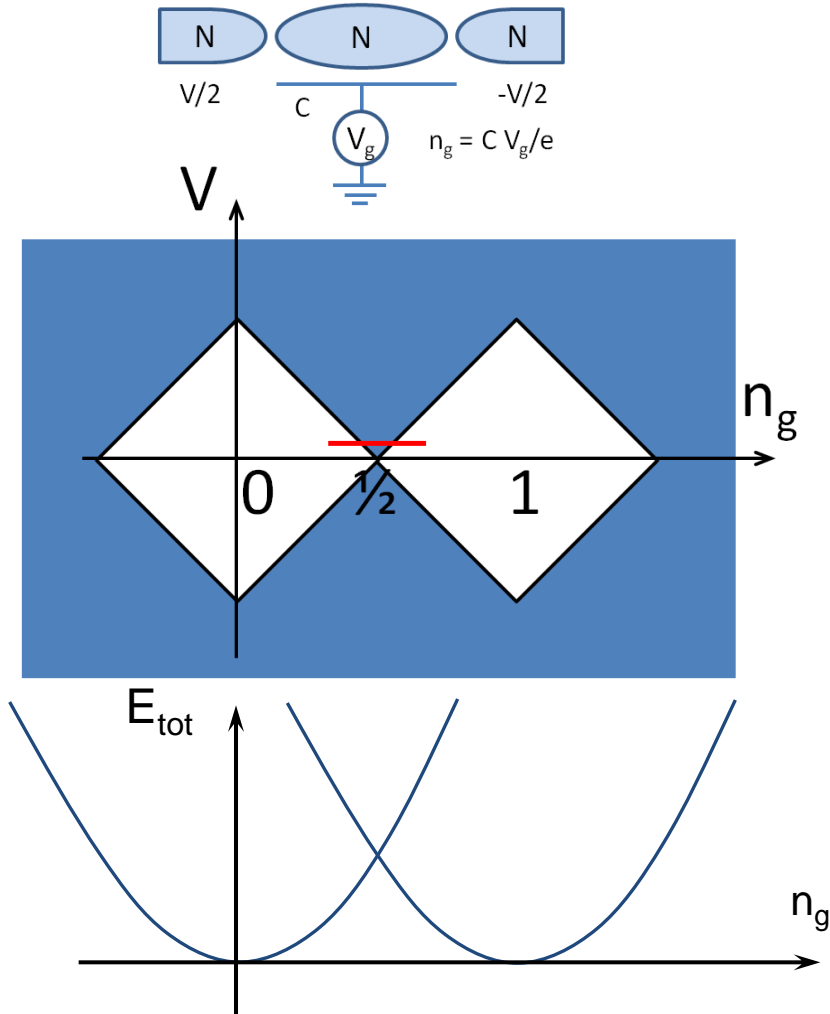
Fast, but difficult to suppress errors

Mechanical shuttles:

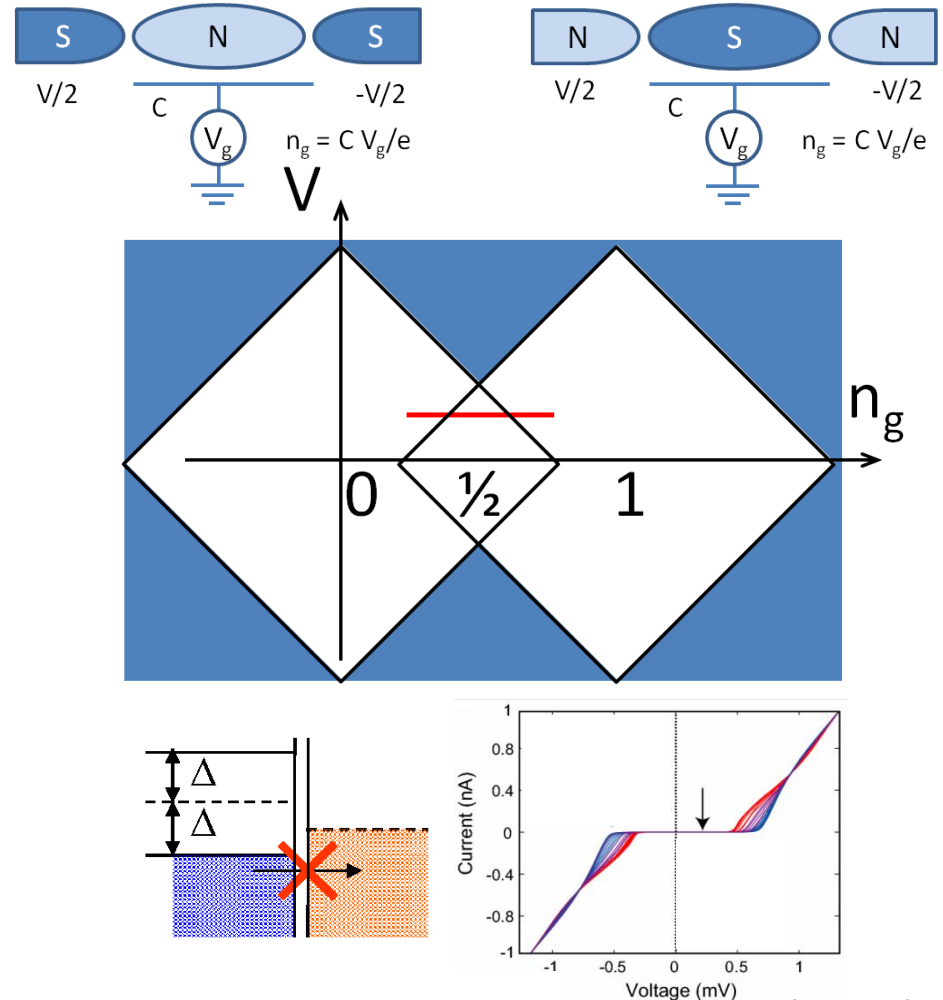
Konig et al. 2008

SET. Principle of electron pumping

Normal state SET



SINIS or NISIN SET



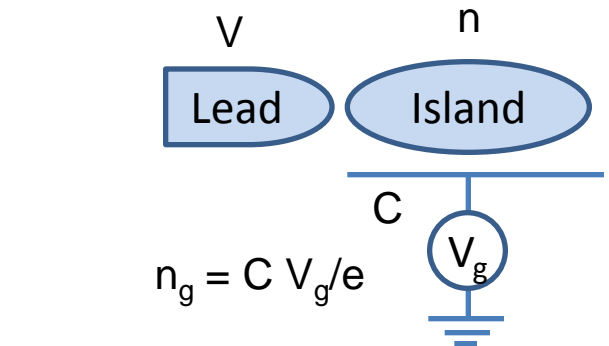
Master equation

$$\hat{H} = \hat{H}_{island}^0 + U_C [\hat{N}] + H_{tunn} + H_{lead}$$

$$\frac{\partial}{\partial t} \hat{\rho} = -\frac{i}{\hbar} [\hat{H}, \hat{\rho}]$$



$$\frac{\partial}{\partial t} p_N = \sum_{N'} (\Gamma_{N' \rightarrow N} p_{N'} - \Gamma_{N \rightarrow N'} p_N)$$



$$U_C [\hat{N}] = E_C \cdot [\hat{N} - n_g(t)]^2$$

$$E_C = e^2 / 2C_\Sigma$$

$$e\Gamma_{N \rightarrow N+1} = I_{L,I}(E_N^+) = \frac{G_T}{e} \int_{-\infty}^{\infty} \rho_L(\varepsilon) \rho_I(\varepsilon + E_N^+) f_L(\varepsilon) [1 - f_I(\varepsilon + E_N^+)] d\varepsilon$$

$$e\Gamma_{N \rightarrow N-1} = I_{I,L}(E_N^-) = \frac{G_T}{e} \int_{-\infty}^{\infty} \rho_L(\varepsilon) \rho_I(\varepsilon - E_N^-) [1 - f_L(\varepsilon)] f_I(\varepsilon - E_N^-) d\varepsilon$$

$$E_N^\pm = U_C[N] - U_C[N \pm 1] \mp eV$$

$$G_T = 4\pi e^2 \nu_n^{(L)} \nu_n^{(I)} \langle |T_{kp}|^2 \rangle$$

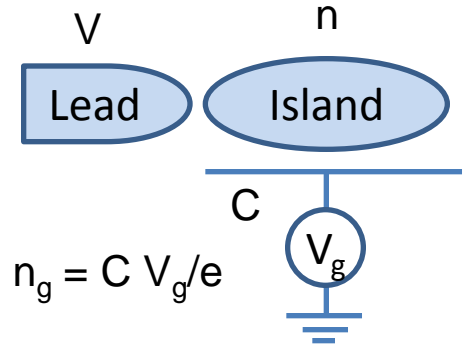
$$\rho_k = \nu_k(E) / \nu_n^{(k)}$$

Master equation

Detailed balance

$$f_L(\varepsilon) = f_I(\varepsilon) = f_{Fermi}(\varepsilon, T)$$

$$\Gamma_{N \rightarrow N \pm 1} = \Gamma_{N \pm 1 \rightarrow N} e^{E_N^\pm / T}$$



Symmetric DOS

$$\rho_k(-\varepsilon) = \rho_k(\varepsilon)$$

$$\Gamma_{N \rightarrow N \pm 1} = \Gamma(E_N^\pm)$$

$$U_C[\hat{N}] = E_C \cdot [\hat{N} - n_g(t)]^2$$

$$\frac{\partial}{\partial t} p_N = \sum_{N'} (\Gamma_{N' \rightarrow N} p_{N'} - \Gamma_{N \rightarrow N'} p_N) \quad E_C = e^2 / 2C_\Sigma$$

$$e\Gamma_{N \rightarrow N+1} = I_{L,I}(E_N^+) = \frac{G_T}{e} \int_{-\infty}^{\infty} \rho_L(\varepsilon) \rho_I(\varepsilon + E_N^+) f_L(\varepsilon) [1 - f_I(\varepsilon + E_N^+)] d\varepsilon$$

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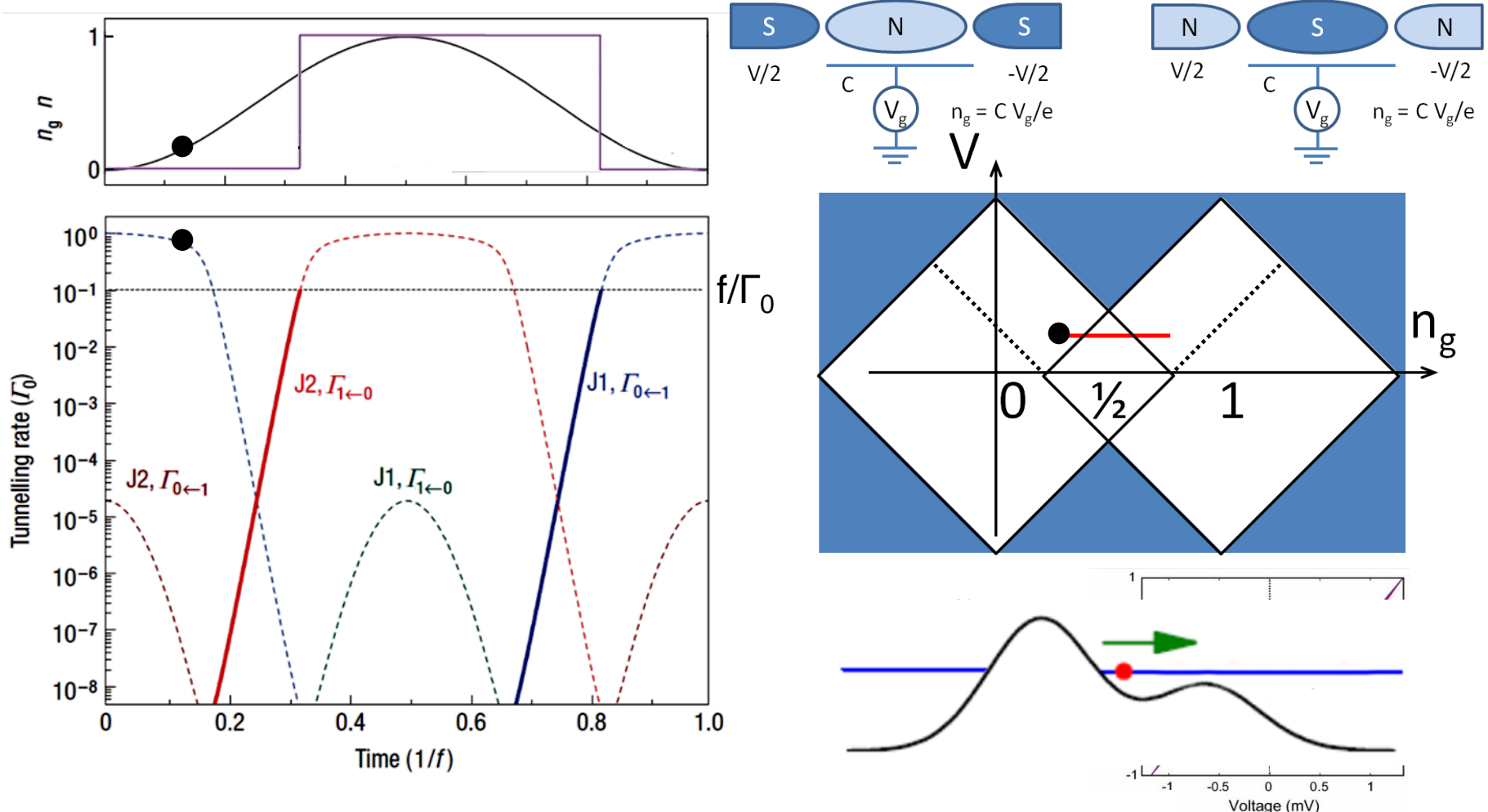
$$E_N^\pm = U_C[N] - U_C[N \pm 1] \mp eV$$

$$G_T = 4\pi e^2 \nu_n^{(L)} \nu_n^{(I)} \langle |T_{kp}|^2 \rangle$$

$$\rho_k = \nu_k(E) / \nu_n^{(k)}$$

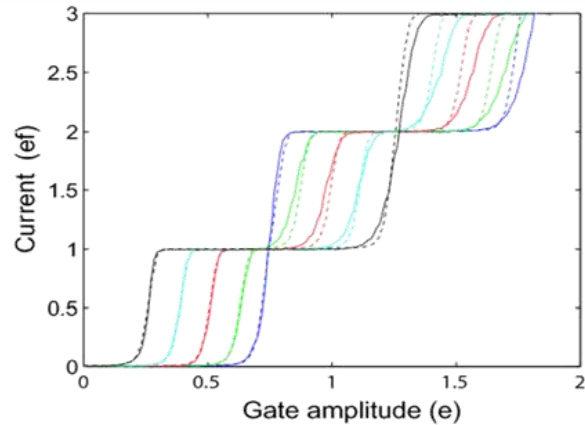
SET. Principle of electron pumping

SINIS or NISIN SET

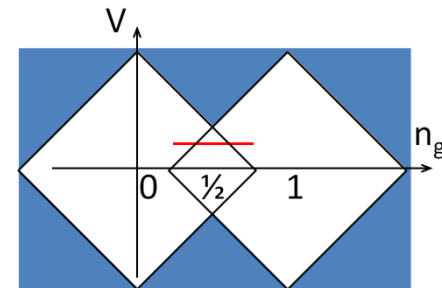
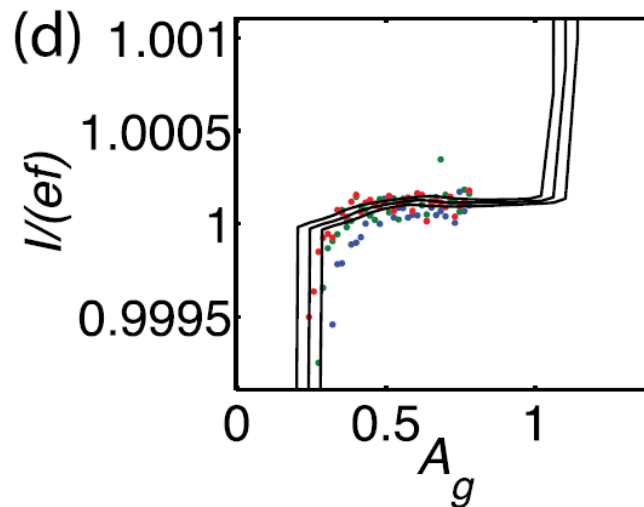
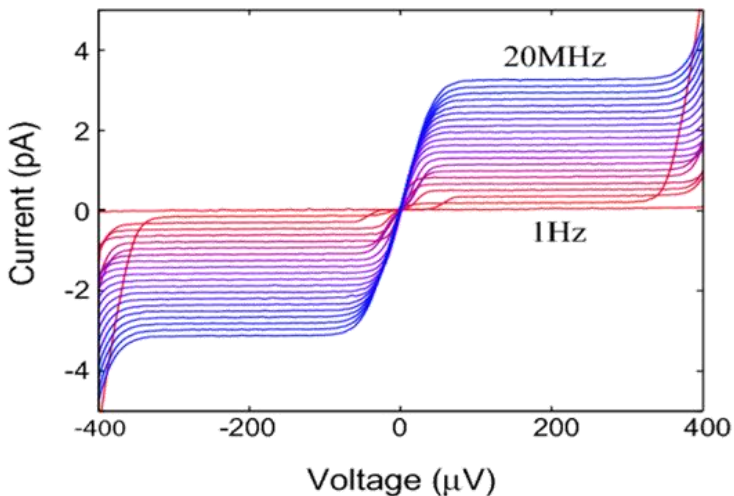
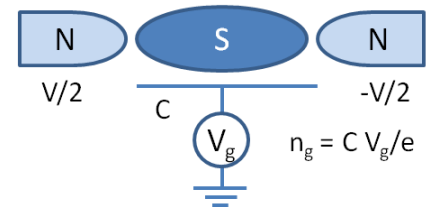
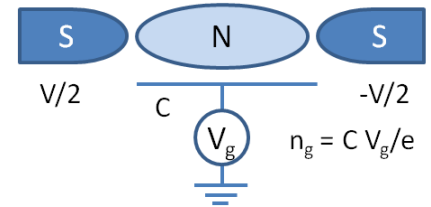
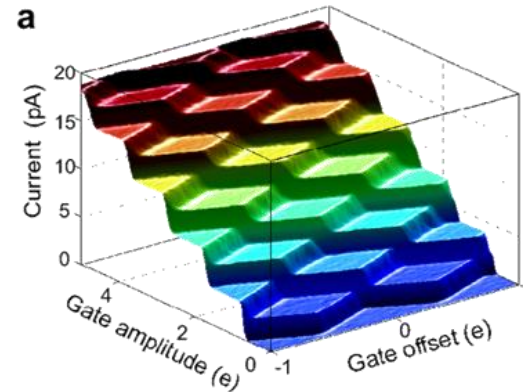


SINIS turnstile. Experimental results

SINIS or NISIN SET



$$I = nef$$



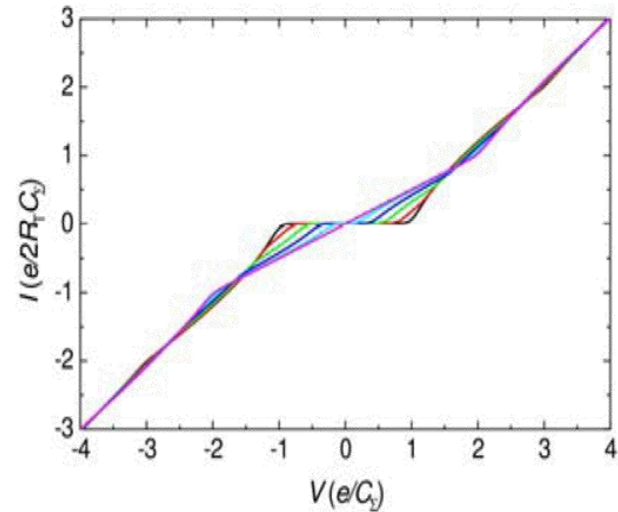
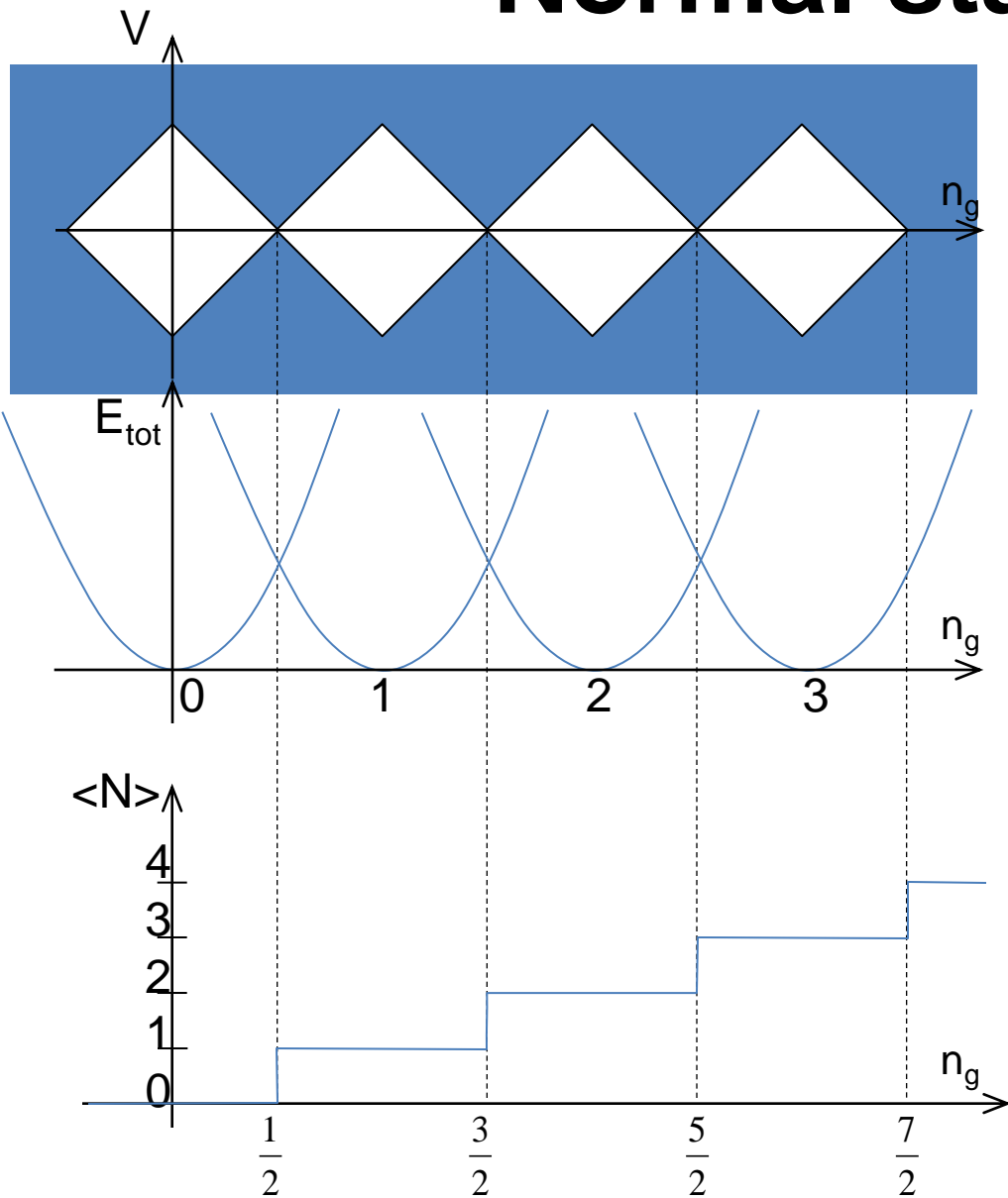
J.P. Pekola et al
Nature Phys. (2008);

Knowles, Maisi, Pekola
APL (2012)

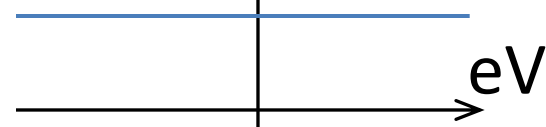
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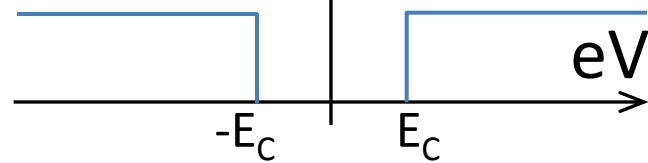
Normal state SET



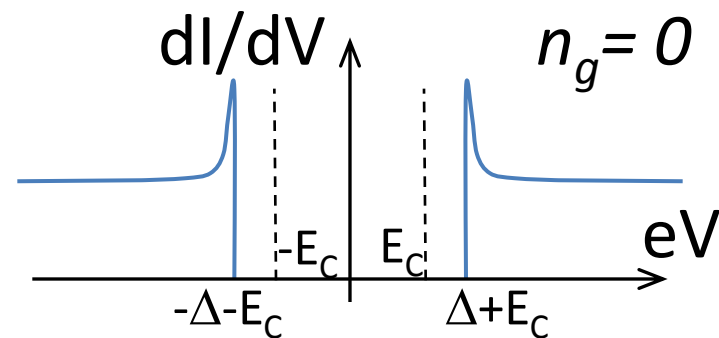
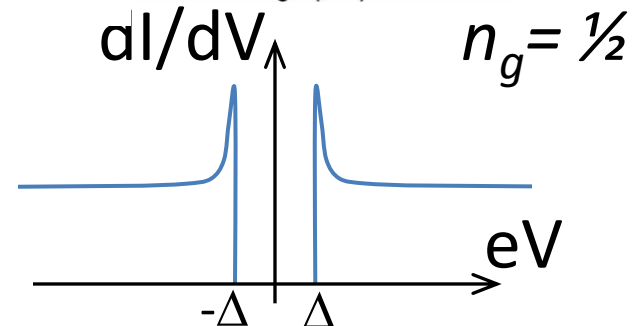
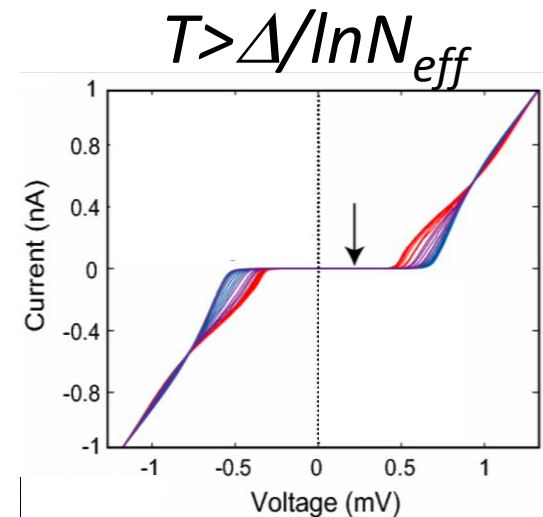
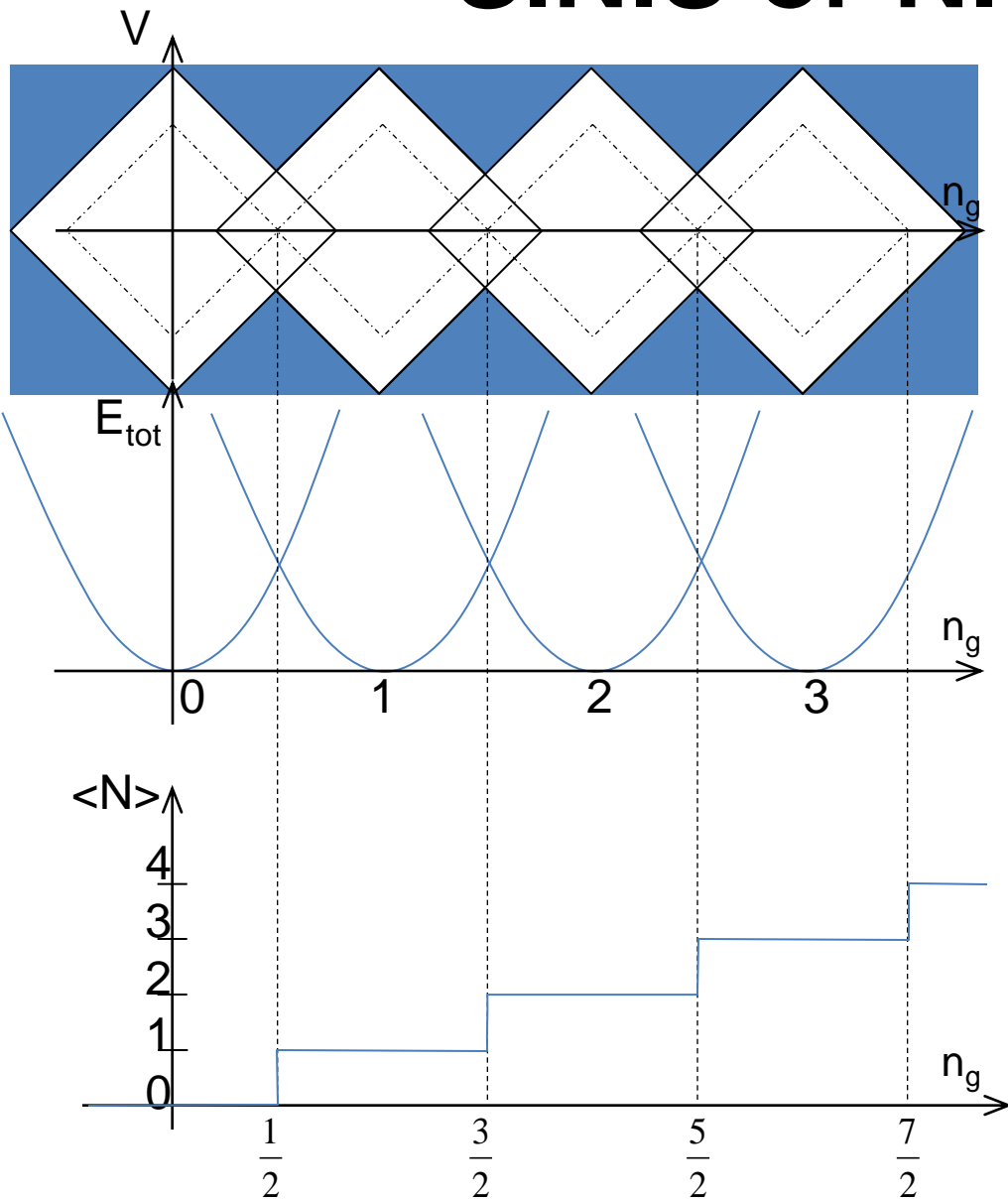
dI/dV $n_g = 1/2$



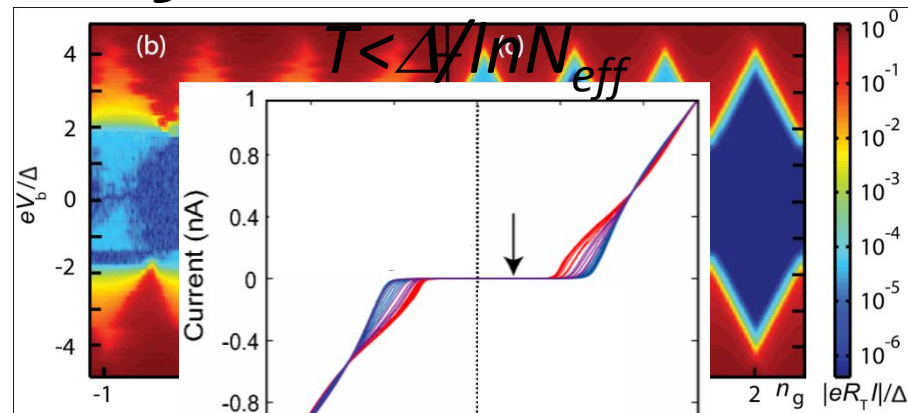
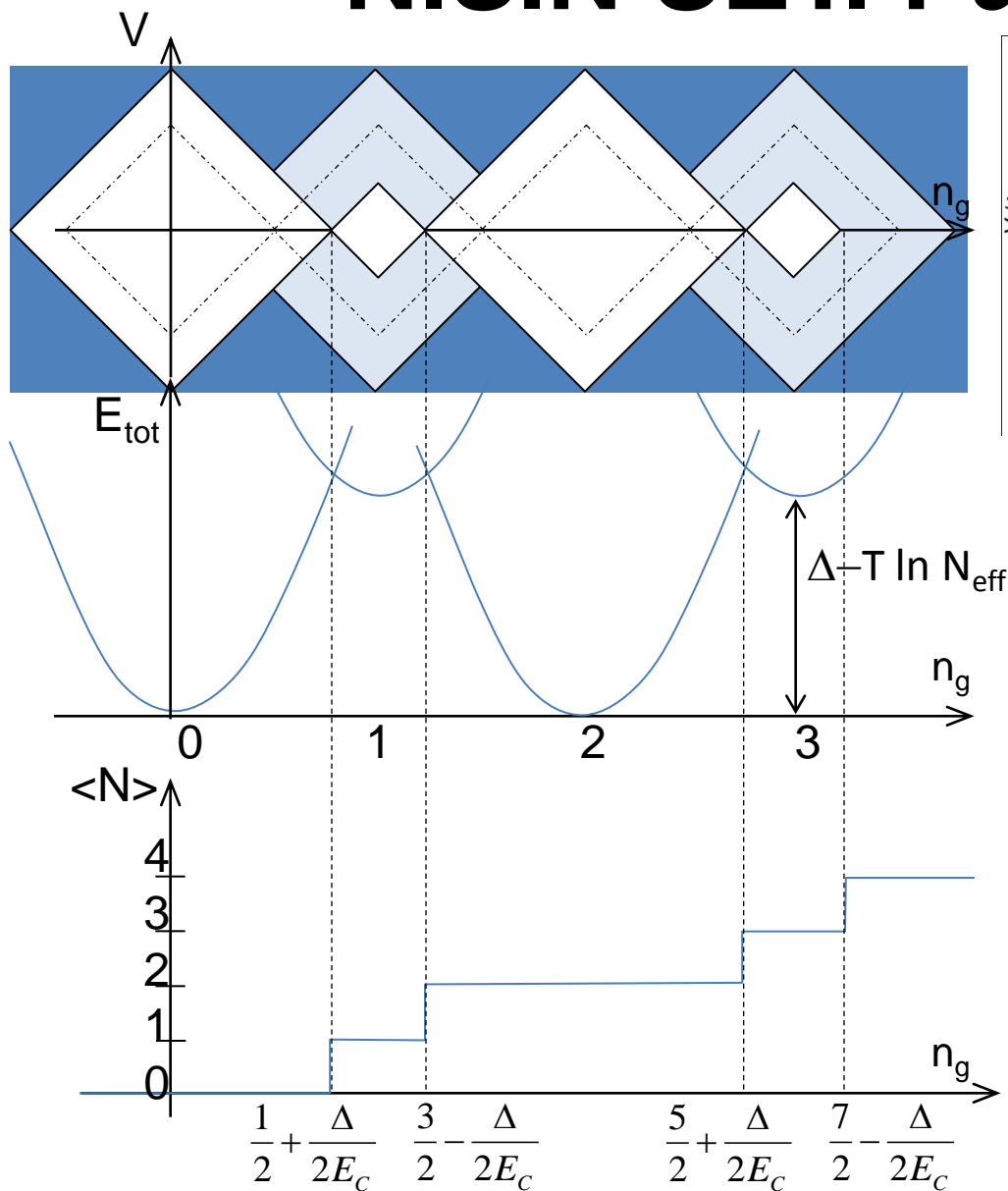
dI/dV $n_g = 0$



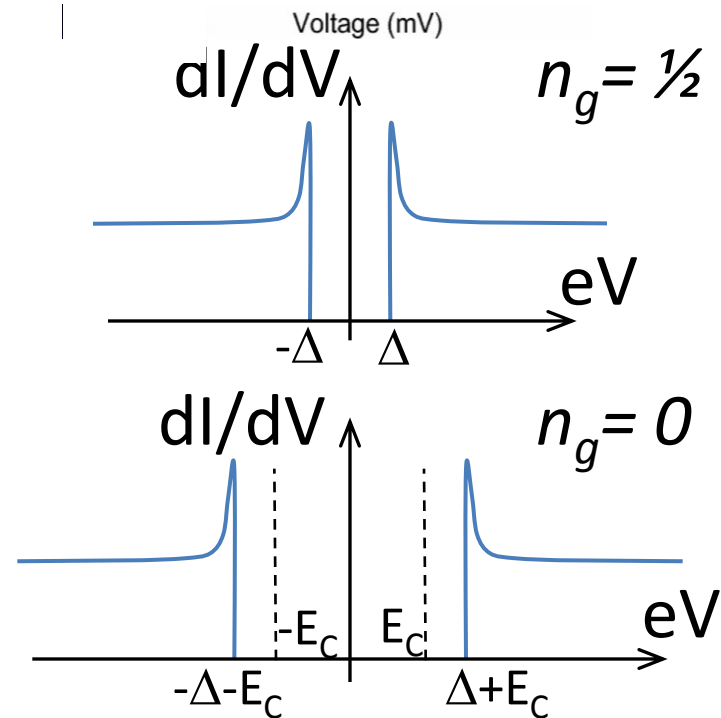
SINIS or NISIN SET



NISIN SET. Parity effect

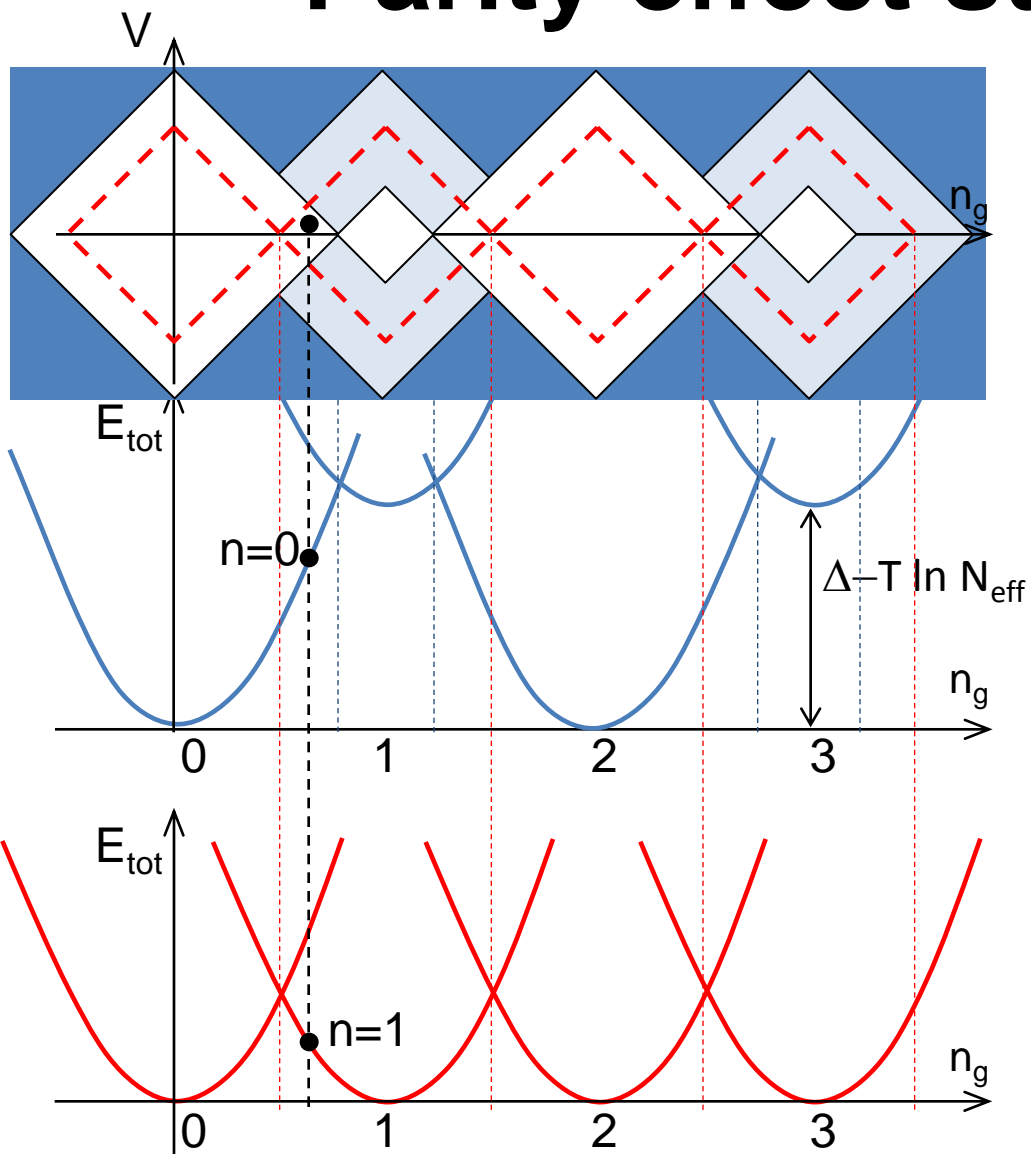


V. Maisi et al PRL 111, 147001 (2013)

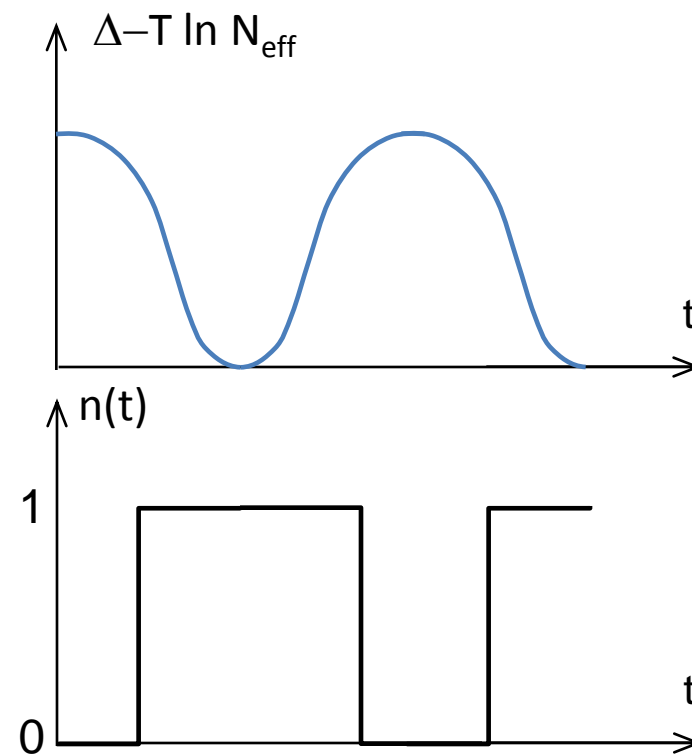


M.T. Tuominen et al PRL, 69, 1997(1992); Averin, Nazarov Physica B 203, 310 (1994)

Parity effect suppression

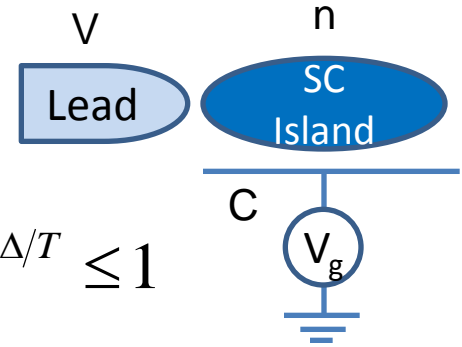


$$\Delta(t) \text{ or } T(t)$$



Master equation with parity effect

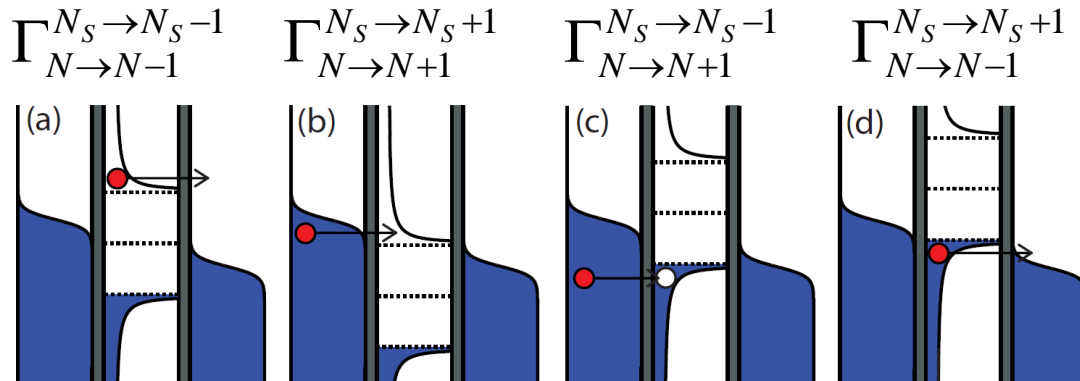
M.T. Tuominen et al PRL, **69**, 1997(1992)
Averin, Nazarov Physica B **203**, 310 (1994)



$$N_{qp} = 2Vv_n \int_0^\infty \rho_S(\varepsilon) f_S(\varepsilon) d\varepsilon \approx N_{eff} e^{-\Delta/T} \leq 1$$

$$N_{eff} = \sqrt{2\pi\Delta T} / \delta \gg 1 \quad \text{normal state interlevel distance} \quad \delta = (Vv_n)^{-1}$$

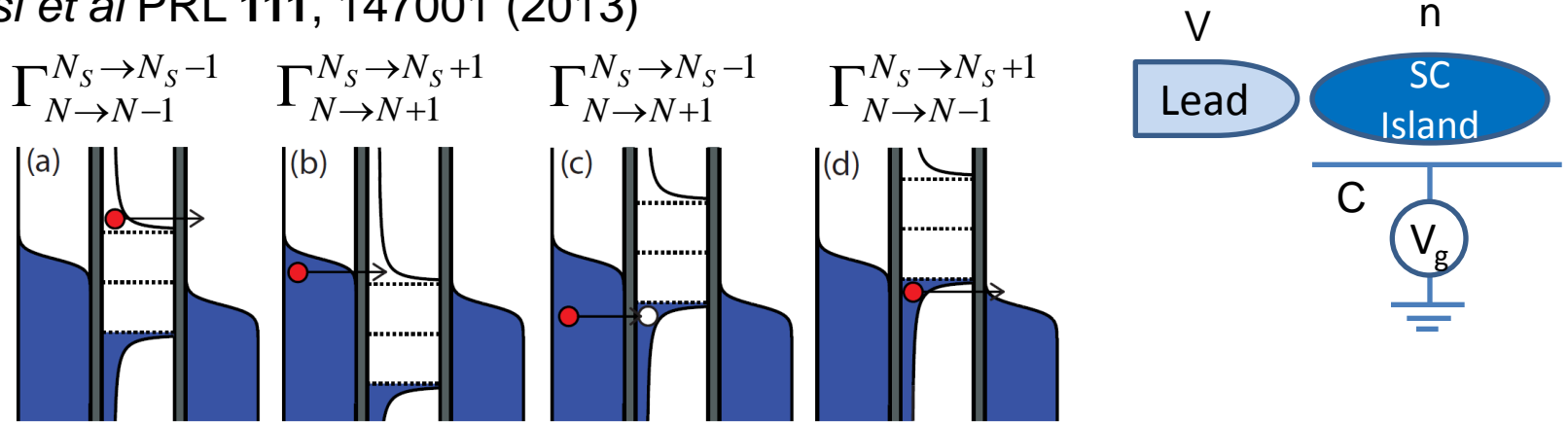
$$\frac{\partial}{\partial t} P_{N,N_S} = \sum_{N',N'_S} \left(\Gamma_{N' \rightarrow N}^{N'_S \rightarrow N_S} P_{N',N'_S} - \Gamma_{N \rightarrow N'}^{N_S \rightarrow N'_S} P_{N,N_S} \right)$$



V. Maisi et al PRL **111**, 147001 (2013)

Master equation with parity effect

V. Maisi et al PRL 111, 147001 (2013)



$$\Gamma_{N \rightarrow N+1}^{N_S \rightarrow N_S+1} = \frac{G_T}{e^2} \int_0^\infty \rho_S(\varepsilon) f_n(\varepsilon - E_N^+) [1 - f_S(\varepsilon, N_S)] d\varepsilon$$

$$\Gamma_{N \rightarrow N+1}^{N_S \rightarrow N_S-1} = \frac{G_T}{e^2} \int_{-\infty}^0 \rho_S(\varepsilon) f_n(\varepsilon - E_N^+) [1 - f_S(\varepsilon, N_S)] d\varepsilon$$

$$\Gamma_{N \rightarrow N-1}^{N_S \rightarrow N_S-1} = \frac{G_T}{e^2} \int_0^\infty \rho_S(\varepsilon) [1 - f_n(\varepsilon + E_N^-)] f_S(\varepsilon, N_S) d\varepsilon$$

$$\Gamma_{N \rightarrow N-1}^{N_S \rightarrow N_S+1} = \frac{G_T}{e^2} \int_{-\infty}^0 \rho_S(\varepsilon) [1 - f_n(\varepsilon + E_N^-)] f_S(\varepsilon, N_S) d\varepsilon$$

$$E_N^\pm = E_C \cdot [\pm 2(n_g - N) - 1] \mp eV$$

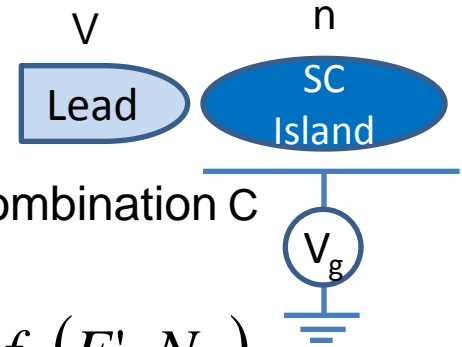
$$G_T = 4\pi e^2 v_n^{(S)} v_n^{(n)} \langle |T_{kp}|^2 \rangle$$

$$\rho_k = v_k(E) / v_n^{(k)}$$

Master equation with parity effect

V. Maisi et al PRL 111, 147001 (2013)

$$N_S = 2Vv_n \int_0^\infty \rho_S(\varepsilon) f_S(\varepsilon, N_S) d\varepsilon$$



Electron-phonon interaction as a channel for quasiparticle recombination C

$$Q_{rec} = V \int_{-\infty}^{\infty} d\xi \int_{-\infty}^{\infty} d\xi' (E + E')^3 \left(1 + \frac{\Delta^2}{EE'}\right) f_S(E, N_S) f_S(E', N_S)$$

$$E = \sqrt{\xi^2 + \Delta^2}$$

$$\Gamma_{N \rightarrow N}^{N_S \rightarrow N_S - 2} \approx \frac{Q_{rec}}{2\Delta} \sim V\Delta^2 n_{qp}^2 = \frac{\Delta^2 N_S^2}{V}$$

If recombination rate is large compared with all tunneling rates, one can reduce the model assuming $N_S = N \bmod 2$

$$\frac{\partial}{\partial t} p_N = \sum_{N', N'_S} \left(\Gamma_{N' \rightarrow N}^{N'_S} p_{N'} - \Gamma_{N \rightarrow N'}^{N_S} p_N \right)$$

$$\Gamma_{N \rightarrow N \pm 1}^0 = \frac{G_T}{e^2} \int_0^\infty \rho_S(\varepsilon) f_n(\varepsilon - E_N^\pm) d\varepsilon \approx \frac{G_T \sqrt{2\pi\Delta T}}{e^2} e^{-(\Delta - E_N^\pm)/T}$$

$$0 < E_N^\pm < \Delta$$

$$\Gamma_{N \rightarrow N \pm 1}^1 = \frac{G_T}{e^2} \int_{-\infty}^{\infty} \rho_S(\varepsilon) f_S(\varepsilon, 1) [1 - f_n(\varepsilon + E_N^\pm)] d\varepsilon \approx \frac{G_T}{2e^2 V v_n}$$

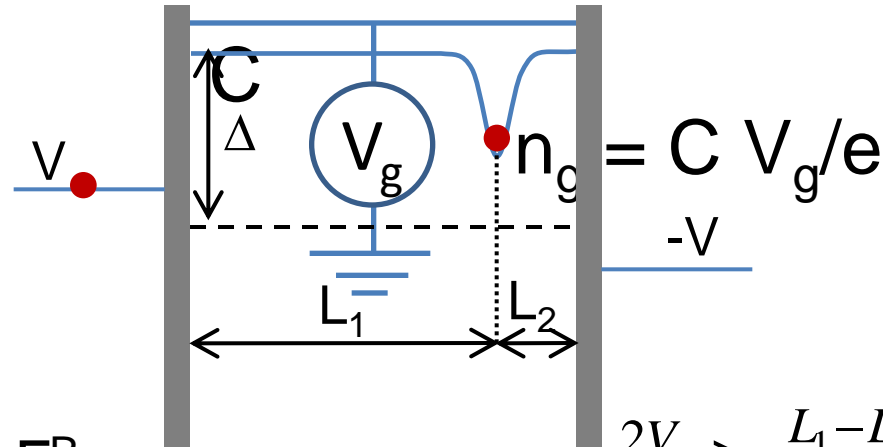
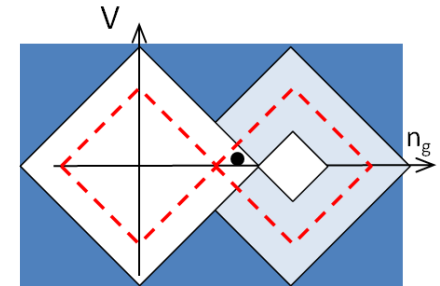
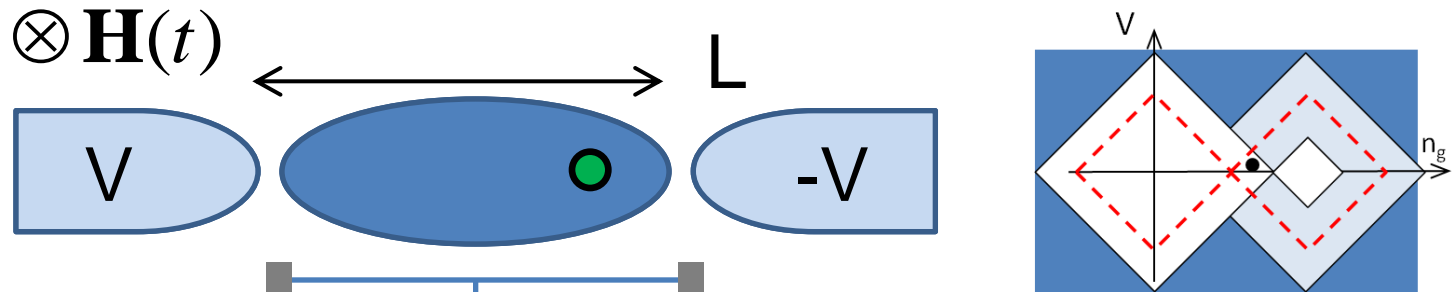
NOTE! There is no detailed balance anymore

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Possible realization.

Superconducting granule with vortex



$1 \rightarrow 0$

$0 \rightarrow 1$

$$L_2 < L_1 \rightarrow \Gamma_{1,0}^L < \Gamma_{1,0}^R$$

$$\frac{2V}{T} > \frac{L_1 - L_2}{\xi} \rightarrow \Gamma_{0,1}^L > \Gamma_{0,1}^R$$

$$\Gamma_{1 \rightarrow 0}^R \sim e^{-L_2/\xi}$$

$$\Gamma_{1 \rightarrow 0}^L \sim e^{-L_1/\xi}$$

$$\Gamma_{0 \rightarrow 1}^R \sim e^{-(\Delta_H + V)/T} e^{-L_2/\xi}$$

$$\Gamma_{0 \rightarrow 1}^L \sim e^{-(\Delta_H - V)/T} e^{-L_1/\xi}$$

Master equation for inhomogeneous granule

$$N_{qp} = 2\nu_n \int_V d^3\mathbf{r} \int_0^\infty \rho_S(\varepsilon, \mathbf{r}) f_S(\varepsilon) d\varepsilon = N_{qp}^0(\Delta) \left[1 - \frac{\xi^2}{R^2} \right] + N_{qp}^0(\Delta_H) \frac{\xi^2}{R^2}$$

$$\rho_S(\varepsilon, \mathbf{r}) = \rho_S^0(\varepsilon, \Delta) \left[1 - e^{-|\mathbf{r}-\mathbf{r}_v|/\xi} \right] + \rho_S^0(\varepsilon, \Delta_H) e^{-|\mathbf{r}-\mathbf{r}_v|/\xi} \quad N_{qp}^0(\Delta) = \sqrt{2\pi\Delta T V} \nu_n e^{-\Delta/T}$$

We assume quasiparticle recombination to be large enough to ensure N_S to be one of the closest integers to N_{qp}

$$N_S = \lfloor N_{qp} \rfloor + (N - \lfloor N_{qp} \rfloor) \bmod 2$$

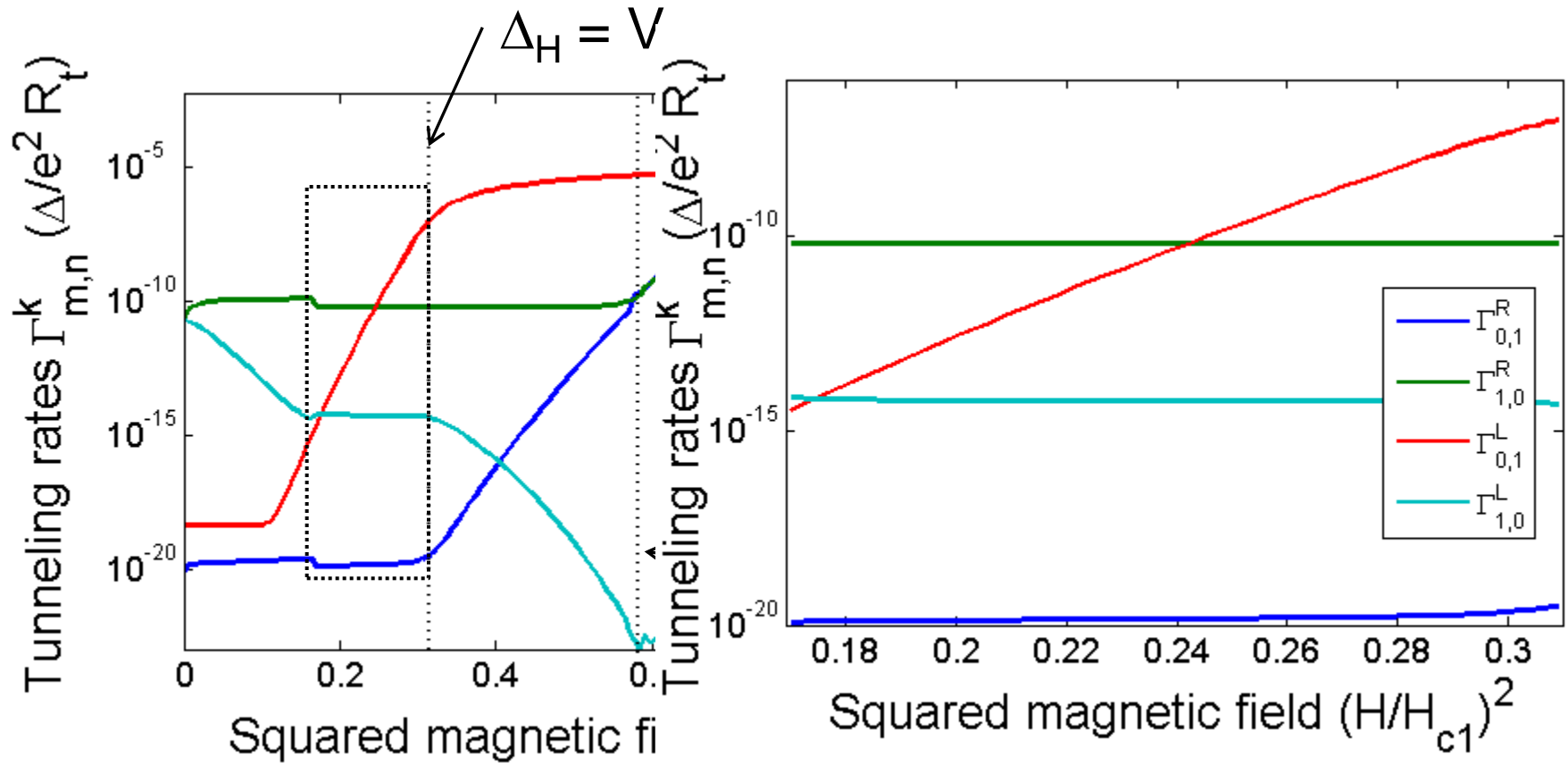
$$\frac{\partial}{\partial t} P_N = \sum_{N', N'_S} \left(\Gamma_{N' \rightarrow N}^{N'_S} P_{N'} - \Gamma_{N \rightarrow N'}^{N_S} P_N \right)$$

$$\Gamma_{N \rightarrow N \pm 1}^0 = \frac{G_T}{e^2} \int_0^\infty \rho_S(\varepsilon, L) f_n(\varepsilon - E_N^\pm) d\varepsilon$$

$$\Gamma_{N \rightarrow N \pm 1}^1 = \frac{G_T}{e^2} \int_{-\infty}^\infty \rho_S(\varepsilon, L) f_S(\varepsilon, 1) \left[1 - f_n(\varepsilon + E_N^\pm) \right] d\varepsilon$$

NOTE! There is no detailed balance anymore

Tunneling rates in NISIN with vortex



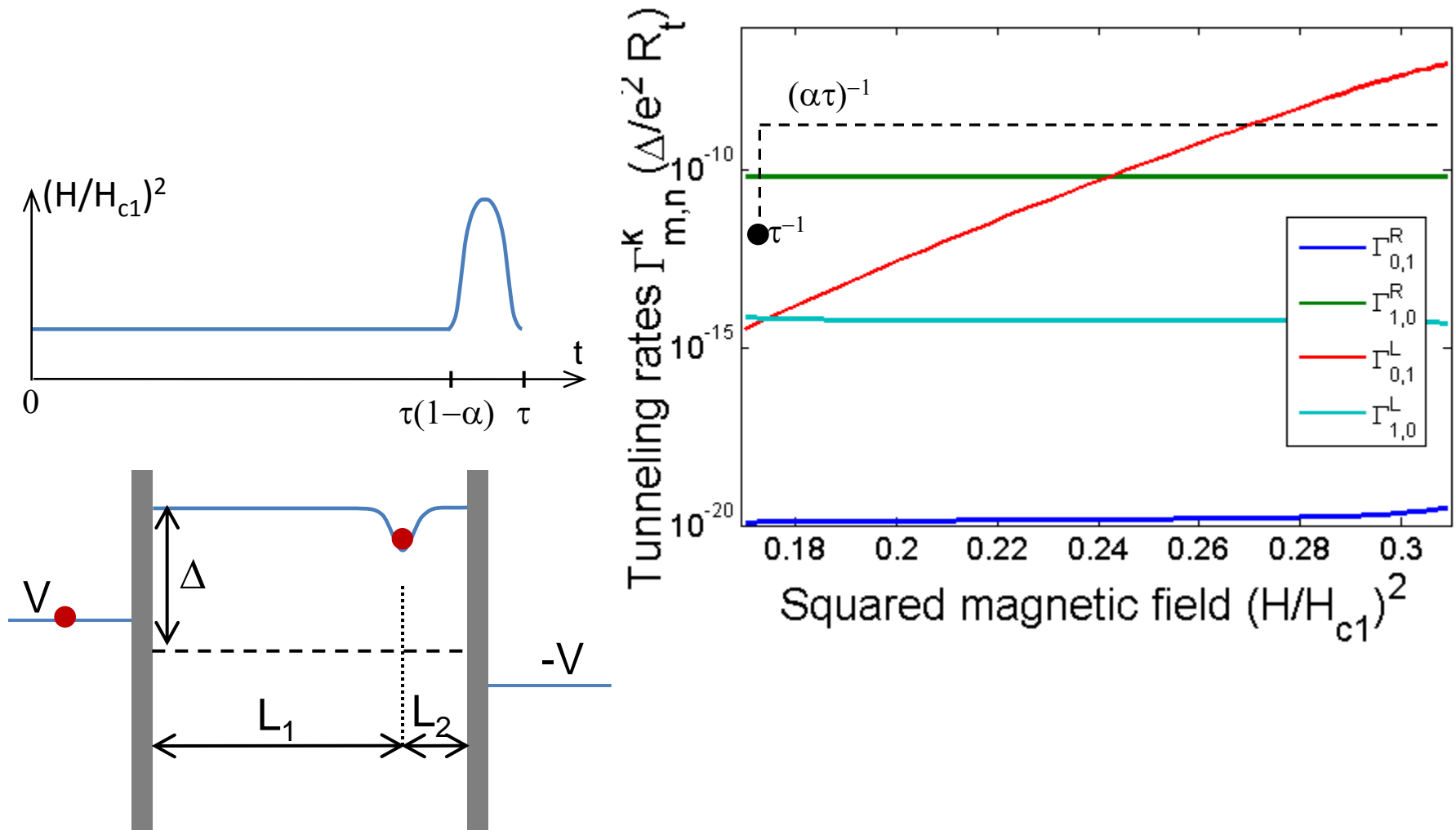
$$\Gamma_{1 \rightarrow 0}^R \sim e^{-L_2/\xi}$$

$$\Gamma_{1 \rightarrow 0}^L \sim e^{-L_1/\xi}$$

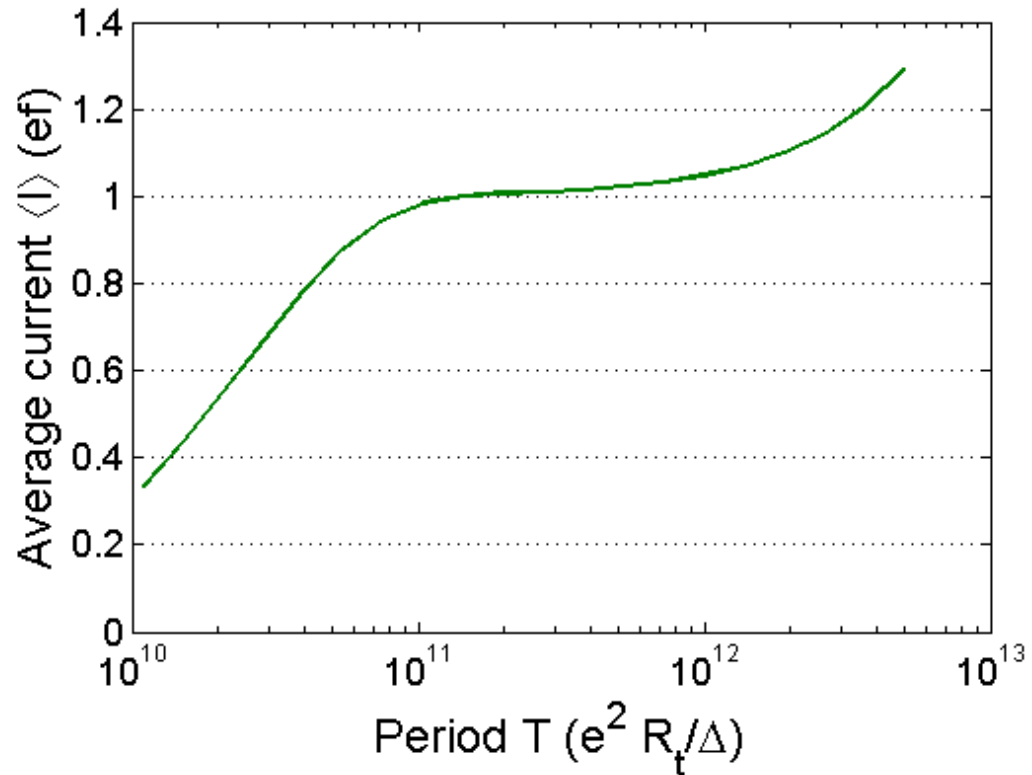
$$\Gamma_{0 \rightarrow 1}^R \sim e^{-(\Delta_H + V)/T} e^{-L_2/\xi}$$

$$\Gamma_{0 \rightarrow 1}^L \sim e^{-(\Delta_H - V)/T} e^{-L_1/\xi}$$

Magnetic field protocol in NISIN



Resulting e-pumping effect



Summary

A new principle of electron pumping based on suppression of parity effect in NISIN single electron transistor is considered.

The time-varying magnetic field is considered as a possible realization of this principle.

Using the rate equation approach the pumping current is calculated as a function of period of the magnetic field cycling.